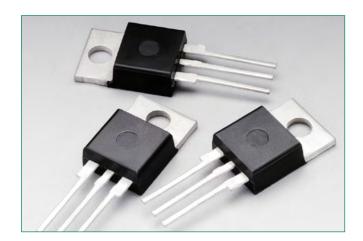
MAC12SM, MAC12SN

TRIACS 600V - 800V







Additional Information







Accessories



Samples

Description

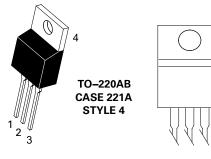
Designed for industrial and consumer applications for full wave control of AC loads such as appliance controls, heater controls, motor controls, and other power switching applications.

Features

- Sensitive Gate Allows Triggering by Microcontrollers and other
- Logic Circuits
- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 70°C
- High Surge Current Capability90 Amperes
- Rugged, Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity

- Maximum Values of IGT, VGT and IH Specified for Ease of Design
- High Commutating di/dt 8.0 A/ms Minimum at 110°C
- Immunity to dV/dt 15 V/sec Minimum at 110°C
- Operational in Three Quadrants: Q1, Q2, and Q3
- These Devices are Pb-Free and are RoHS Compliant*

Pin Out



Functional Diagram





^{*}RoHS-compliant and lead-free

Maximum Ratings $(T_1 = 25^{\circ}C \text{ unless otherwise noted})$

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) MAC12SM (Gate Open, Sine Wave 50 to 60 Hz, $T_J = 40$ to 110°C) MAC12SN		V _{DRM} , V _{RRM}	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 7$	I _{T (RMS)}	12	А	
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T, = 110°C)		I _{TSM}	100	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	33	A²sec	
Peak Gate Power (Pulse Width $\leq 1.0 \mu s$, $T_c = 70^{\circ}C$)	P _{GM}	16	W	
Average Gate Power (t = 8.3 ms , $T_c = 70^{\circ}\text{C}$)		$P_{G(AV)}$	0.35	W
Operating Junction Temperature Range		T_{J}	-40 to +110	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{ejc} R _{eja}	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		T _L	260	°C

Electrical Characteristics - OFF (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T, = 25°C	I _{DRM} ,	-	-	0.01	mΛ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_{J}^{\circ} = 110^{\circ}C$	I	-	-	2.0	mA

Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A}$)		V_{TM}	-	-	1.85	V
Gate Trigger Current	MT2(+), G(+)		-	1.5	5.0	mA
(Continuous dc)	MT2(+), G(-)	I _{GT}	-	2.5	5.0	
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		-	2.7	5.0	
Holding Current ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = $\pm 20 \text{ C}$	00 mA))	I _H	-	2.5	10	mA
	MT2(+), G(+)		-	3.0	15	mA
Latching Current $(V_D = 12 \text{ V, } I_G = 5 \text{ mA})$	MT2(+), G(-)	IL	-	5.0	20	
(V _D = 12 V, I _G = 3 111A)	MT2(-), G(-)		-	3.0	15	
O + T: VIII	MT2(+), G(+)		0.45	0.68	1.5	
Gate Trigger Voltage $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega)$	MT2(+), G(-)	$V_{\rm GT}$	0.45	0.62	1.5	V
	MT2(-), G(-)		0.45	0.67	1.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%



^{1.} V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

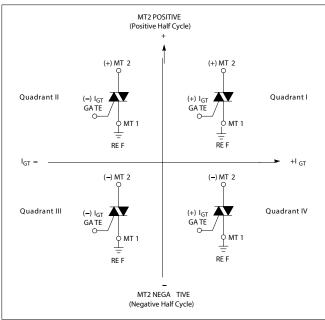
Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Change of Commutating Current (V _D = 400 V, I _{TM} = 3.5 A, Commutating dv/dt = 10 V/ μ s, Gate Open, T _J = 110 °C, f = 500 Hz, Snubber: C _s = 0.01 μ f, R _s = 15 Ω)	(dv/dt) _C	8.0	10	-	A/ms
Critical Rate of Rise of Off-State Voltage ($V_D=67 \% V_{DRM}$, Exponential Waveform, $R_{GK}=1 \text{ K}$, $T_J=110 \degree \text{C}$)	dV/dt	15	40	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 100 mA/µsec; lgt = 100 mA; f = 60 Hz	di/dt	_	_	10	A/µs

Voltage Current Characteristic of SCR

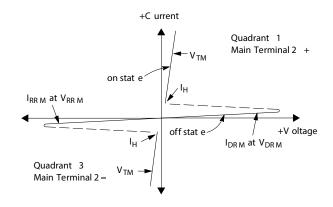
Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All polarities are referenced to MT1.

 $\dot{\rm With}$ in –phase signals (using standard AC lines) quadrants I and III are used





MAC12SM, MAC12SN TRIACS 600V - 800V

Figure 1.Typical Gate Trigger Current vs Junction Temperature

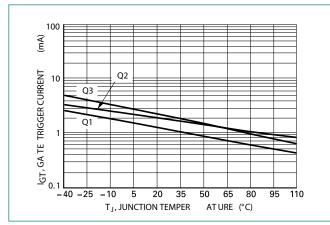


Figure 2.Typical Gate Trigger Voltage vs Junction Temperature

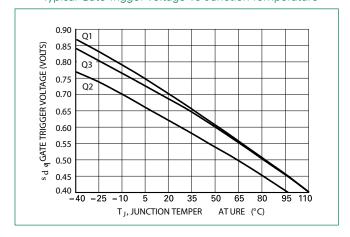


Figure 3.Typical Holding Current vs Junction Temperature

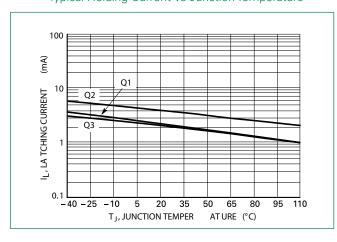


Figure 4.Typical Latching Current vs Junction Temperature

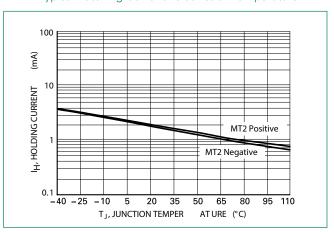


Figure 5.Typical RMS Current Derating

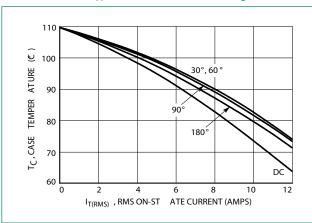
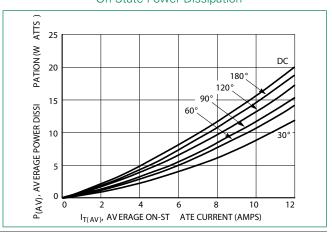


Figure 6.On-State Power Dissipation





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Figure 7.Typical On-State Characteristics

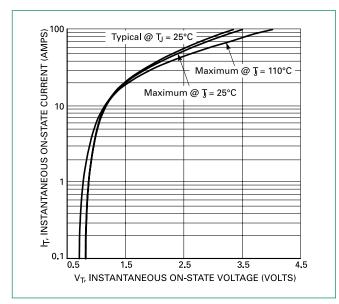
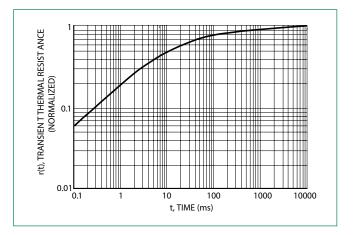


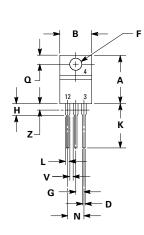
Figure 8.Typical Thermal Response

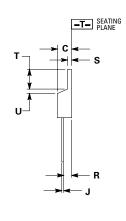




MAC12SM, MAC12SN TRIACS 600V - 800V

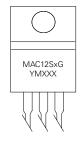
Dimensions





Part Marking System





=M or N =Year =Month XXX =Lot Trace Code =Pb-Free Package

Dim	Inches		Millimeters			
Dilli	Min	Max	Min	Max		
Α	0.590	0.620	14.99	15.75		
В	0.380	0.420	9.65	10.67		
С	0.178	0.188	4.52	4.78		
D	0.025	0.035	0.64	0.89		
F	0.142	0.147	3.61	3.73		
G	0.095	0.105	2.41	2.67		
Н	0.110	0.130	2.79	3.30		
J	0.018	0.024	0.46	0.61		
K	0.540	0.575	13.72	14.61		
L	0.060	0.075	1.52	1.91		
N	0.195	0.205	4.95	5.21		
Q	0.105	0.115	2.67	2.92		
R	0.085	0.095	2.16	2.41		
S	0.045	0.060	1.14	1.52		
Т	0.235	0.255	5.97	6.47		
U	0.000	0.050	0.00	1.27		
V	0.045		1.15			
Z		0.080		2.04		

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

Ordering Information

Device	Package	Shipping
MAC12SMG	TO-220AB	1000 Unito / Poy
MAC12SNG	(Pb-Free)	1000 Units / Box



Dimensioning and tolerancing per ansi y14.5m, 1982.
 Controlling dimension: inch.

^{3.} Dimension z defines a zone where all body and lead irregularities are allowed.